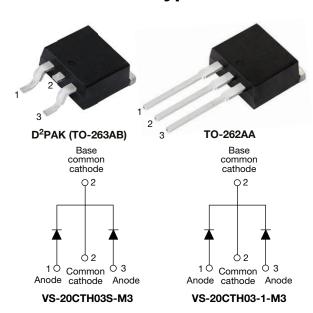


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Vishay Semiconductors

Hyperfast Rectifier, 2 x 10 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 10 A							
V _R	300 V							
V _F at I _F	0.85 V							
t _{rr} max.	35 ns							
T _J max.	175 °C							
Package	D ² PAK (TO-263AB), TO-262AA							
Circuit configuration	Common cathode							

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature



- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Meets JESD 201, class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Terminal: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage	V_{RRM}		300	V				
Average rectified forward current per diode	IE/A\A	T _C = 160 °C	10					
per device			20	Α				
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	120					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MA								
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	$I_R = 100 \ \mu A$	300	-	-			
Forward voltage	V _F	I _F = 10 A	-	1.05	1.25	V		
Forward voltage		I _F = 10 A, T _J = 125 °C	-	0.85	0.95			
Reverse leakage current	I _R	$V_R = V_R$ rated	-	-	20			
neverse leakage current		T _J = 125 °C, V _R = V _R rated	-	6	200	- μΑ		
Junction capacitance	C _T	V _R = 300 V	-	30	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH		

VS-20CTH03S-M3, VS-20CTH03-1-M3

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$50 \text{ A/}\mu\text{s}, V_{\text{R}} = 30 \text{ V}$	ı	-	35	
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		ı	-	30	1
		T _J = 25 °C		-	31	=.	ns
		T _J = 125 °C		-	42	=.	
Dools was a sure of the sure o	I _{RRM}	T _J = 25 °C	I _F = 10 A dI _F /dt = 200 A/µs	-	2.4	-	A nC
Peak recovery current		T _J = 125 °C	V _R = 200 V	-	5.6	=.	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	36	-	
		T _J = 125 °C		-	120	-	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case per diode	R _{thJC}		-	-	1.5	°C/W		
Thermal resistance, junction to ambient	R _{thJA}		-	-	70	°C/W		
Weight			-	2.0	-	g		
vveignt			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking davisa		Case style D ² PAK (TO-263AB)		20CT	H03S			
Marking device		Case style TO-262AA 20			H03-1			

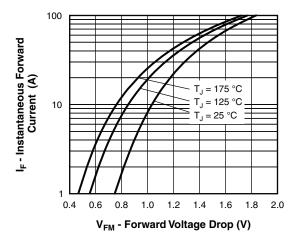


Fig. 1 - Maximum Forward Voltage Drop Characteristics

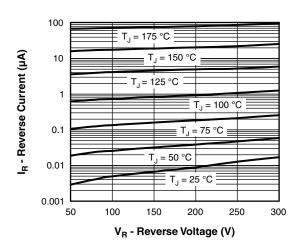


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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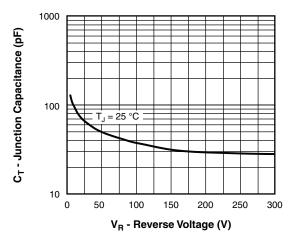


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

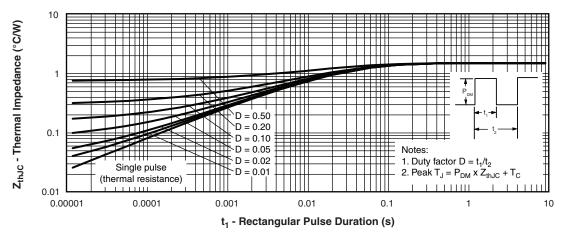


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

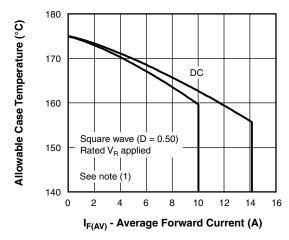


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

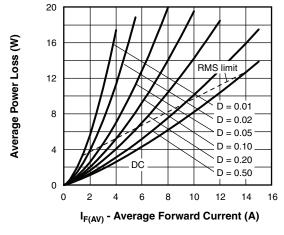


Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{th,JC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R



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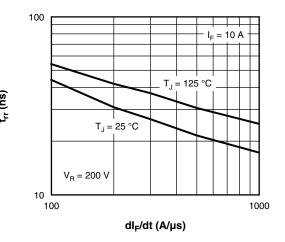


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

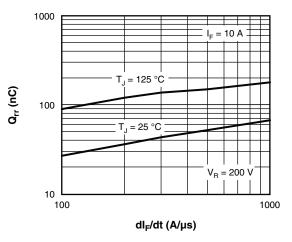
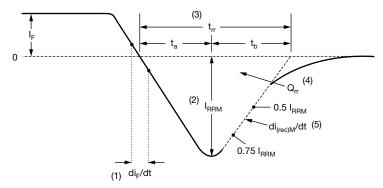


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RBM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

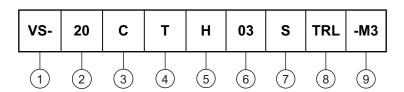
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-20CTH03S-M3, VS-20CTH03-1-M3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Current rating (20 A)

3 - C = common cathode

- $T = TO-220, D^2PAK (TO-263AB)$

5 - H = hyperfast rectifier

6 - Voltage rating (03 = 300 V)

7 - • S = D^2PAK (TO-263AB)

• -1 = TO-262AA

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK (TO-263AB) package)

• TRR = tape and reel (right oriented, for D²PAK (TO-263AB) package)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

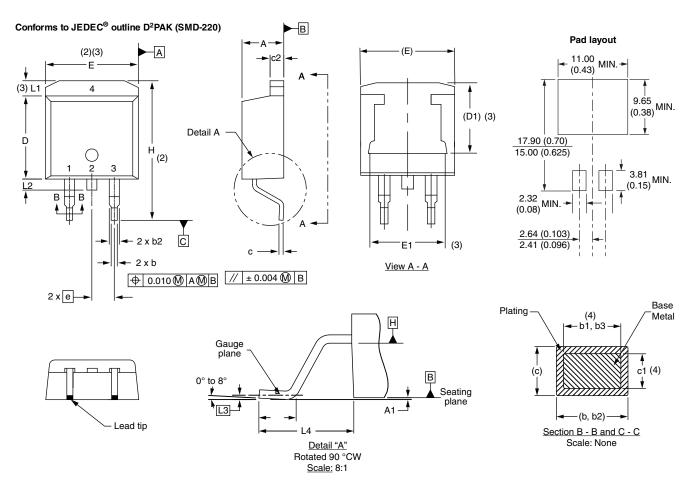
LINKS TO RELATED DOCUMENTS							
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164					
Differsions	TO-262AA	www.vishay.com/doc?96165					
Dart marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444					
Part marking information	TO-262AA	www.vishay.com/doc?95443					
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424					
SPICE model		www.vishay.com/doc?96583					



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWD	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

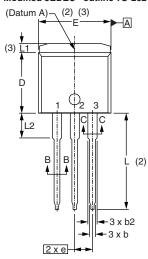
Revision: 13-Jul-17 **1** Document Number: 96164

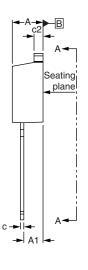
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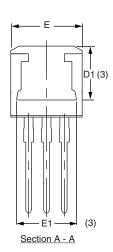
TO-262AA

DIMENSIONS in millimeters and inches

Modified JEDEC® outline TO-262







⊕ 0.010 **M** A**M** B

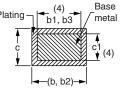
Lead assignments



Diodes 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

				Т	
SYMBOL	MILLIN	IETERS	INC	NOTES	
OTHIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	=	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

Revision: 30-Nov-17 Document Number: 96165

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



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